

Rev.F Mar.-2016

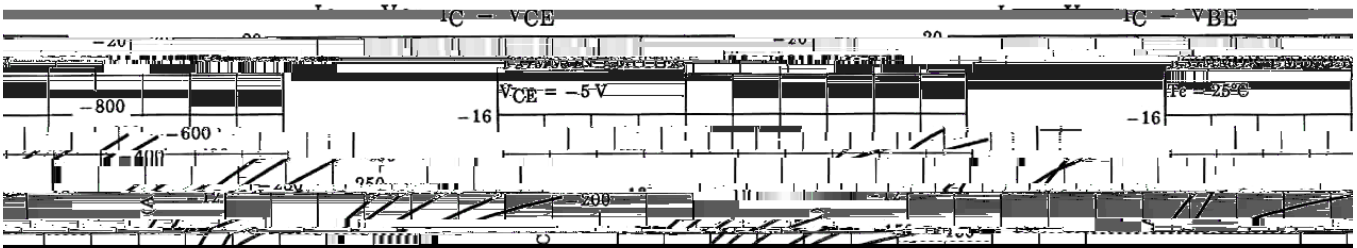
Silicon PNP transistor in a TO-3P Plastic Package.

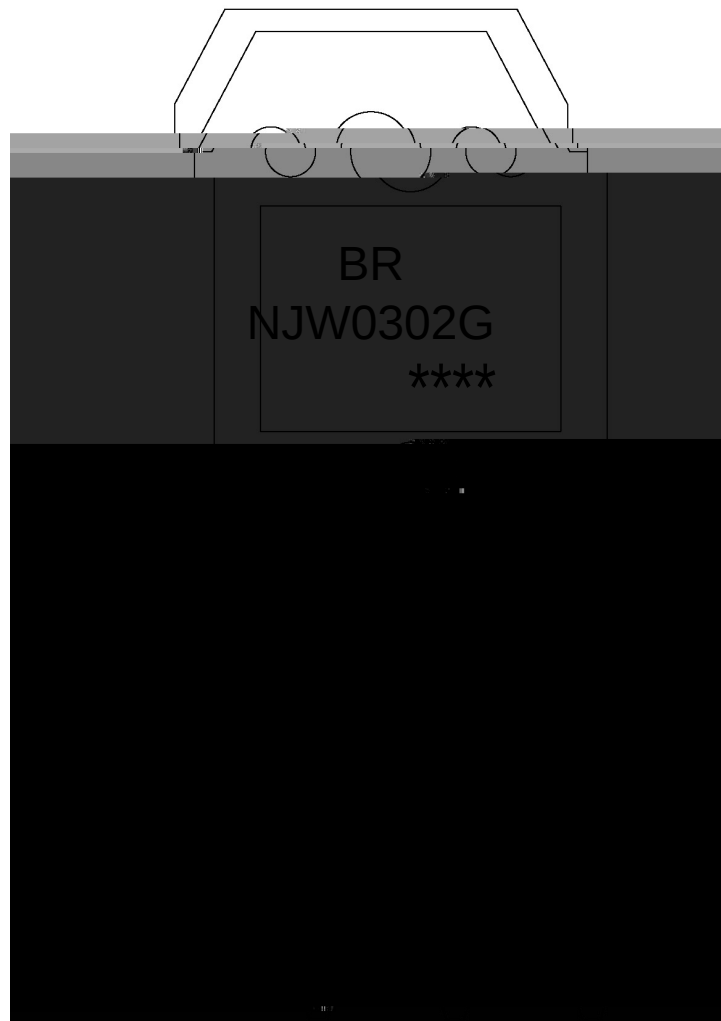
Recommend for 100W high fidelity audio frequency amplifier output stage, Complementary to

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-230	V
Collector to Emitter Voltage	V_{CEO}	-230	V
Emitter to Base Voltage	V_{EBO}	-5	V
Collector Current - Continuous	I_C	-15	A
Peak Collector Current	I_{CP}	-30	A
Base Current	I_B	-1.5	A
Collector Power Dissipation	$P_{C(TC=25)}$	150	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=-50mA$ $I_B=0$	-230			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=-230V$ $I_E=0$			-5.0	A
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=-5.0V$ $I_C=0$			-5.0	A
DC Current Gain	$h_{FE(1)}$	$V_{CE}=-5.0V$ $I_C=-1.0A$	55		160	
	$h_{FE(2)}$	$V_{CE}=-5.0V$ $I_C=-7.0A$	35	60		
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-8.0A$ $I_B=-0.8A$		-1.5	-3.0	V
Base to Emitter Voltage	V_{BE}	$V_{CE}=-5.0V$ $I_C=-7.0A$		-1.0	-1.5	V
Transition Frequency	f_T	$I_C=-1.0A$ $V_{CE}=-5.0V$	30		MHz	

Rev.F Mar.-2016





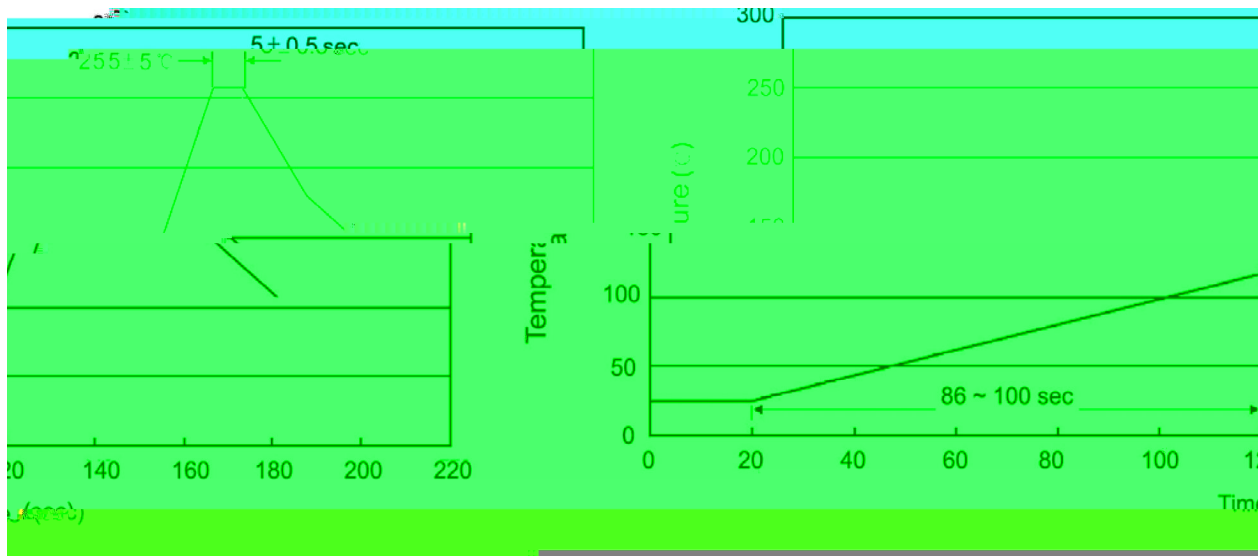
Note:

BR: Company Code.

NJW0302G: Product Type.

****: Lot No. Code, code change with Lot No.

Rev.F Mar.-2016



Note:

1. 25 ~ 150 °C, Time: 60 ~ 90sec;
2. 255 ± 5 °C, Duration: 5 ± 0.5sec;
3. Cooling Speed: 2 ~ 10 °C/sec.

1. Preheating: 25~150 °C, Time: 60~90sec.
2. Peak Temp.: 255 ± 5 °C, Duration: 5 ± 0.5sec.
3. Cooling Speed: 2~10 °C/sec.

4sDimens4 T9914406(d: 2~1)-f 1 (10)20.65 11R Tf 1.6632 0 86 367116d>T745<045 54ca-5.7